



Cite this: *J. Mater. Chem. C*, 2023,
11, 11091

Correction: Solution-processable Li-doped transition metal oxide hole-injection layer for highly efficient quantum-dot light-emitting diodes

Jae Seung Shin,^{ab} Mingye Kim,^{ab} Jin Hyun Ma,^a Jun Hyung Jeong,^a
Hui Ung Hwang,^{cd} Jeong Won Kim^{cd} and Seong Jun Kang^{*ab}

DOI: 10.1039/d3tc90173d

rsc.li/materials-c

Correction for 'Solution-processable Li-doped transition metal oxide hole-injection layer for highly efficient quantum-dot light-emitting diodes' by Jae Seung Shin *et al.*, *J. Mater. Chem. C*, 2022, **10**, 5590–5597, <https://doi.org/10.1039/D1TC06117H>.

The authors regret that one of the authors' names (Hui Ung Hwang) was spelled incorrectly in the originally published article. The correct spelling is as shown above.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.



^a Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University, Yongin, 17104, Republic of Korea. E-mail: junkang@khu.ac.kr; Tel: +82-31-201-3324

^b Integrated Education Institute for Frontier Science & Technology (BK21 Four), Kyung Hee University, Yongin, 17104, Republic of Korea

^c Korea Research Institute of Standards and Science (KRISS), 267 Gajeong-ro, Daejeon, 34113, South Korea

^d University of Science and Technology (UST), 217 Gajeong-ro, Daejeon, 34113, South Korea